

MBR1060

SWITCHMODE™ Power Rectifiers

Features

- Guard-Ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- Pb-Free Packages are Available*

Mechanical Characteristics

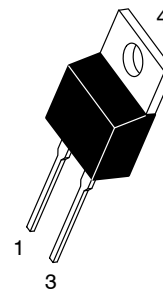
- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B
Machine Model = C



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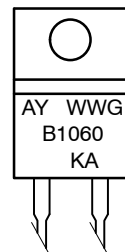
<http://onsemi.com>

**SCHOTTKY BARRIER
RECTIFIERS
10 AMPERES, 60 VOLTS**



**TO-220AC
CASE 221B
PLASTIC**

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package
B1060 = Device Code
KA = Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping
MBR1060	TO-220	50 Units/Rail
MBR1060G	TO-220 (Pb-Free)	50 Units/Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR1060

MAXIMUM RATINGS

Rating	Symbol	MBR1060	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	60	V
Average Rectified Forward Current (Rated V_R) $T_C = 133^\circ\text{C}$	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz) $T_C = 133^\circ\text{C}$	I_{FRM}	20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz)	I_{RRM}	0.5	A
Operating Junction Temperature (Note 1)	T_J	-65 to +175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.0	$^\circ\text{C/W}$
Maximum Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	60	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 10$ Amps, $T_C = 125^\circ\text{C}$) ($i_F = 10$ Amps, $T_C = 25^\circ\text{C}$) ($i_F = 20$ Amps, $T_C = 125^\circ\text{C}$) ($i_F = 20$ Amps, $T_C = 25^\circ\text{C}$)	v_F	0.7 0.8 0.85 0.95	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^\circ\text{C}$) (Rated dc Voltage, $T_C = 25^\circ\text{C}$)	i_R	22 0.10	mA

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

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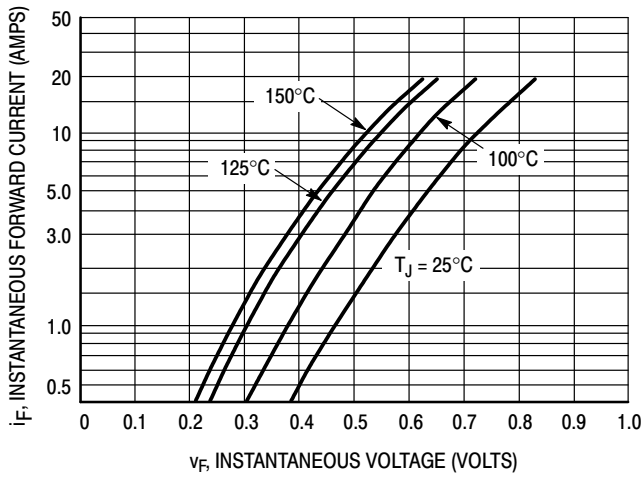


Figure 1. Typical Forward Voltage

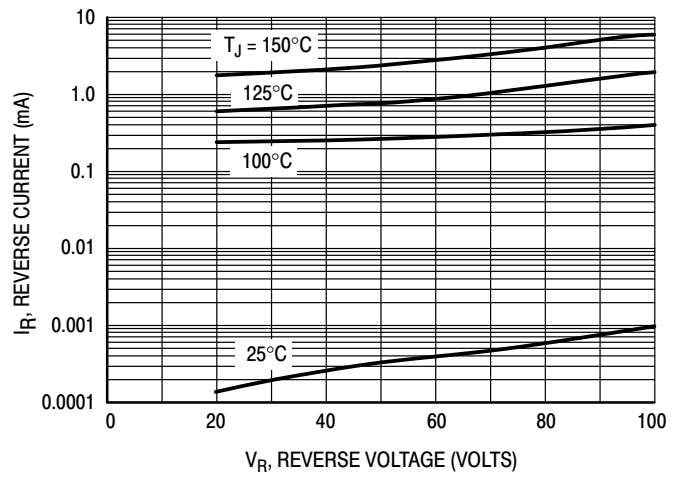


Figure 2. Typical Reverse Current

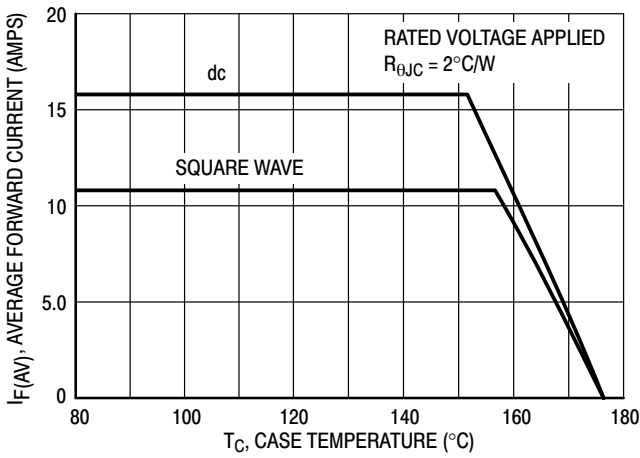


Figure 3. Typical Current Derating, Case

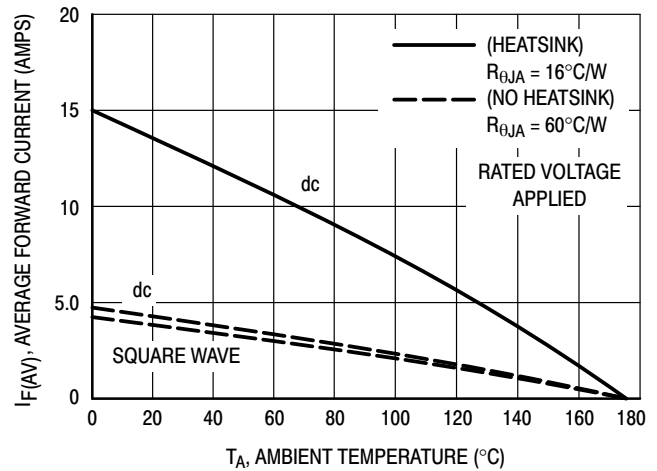


Figure 4. Typical Current Derating, Ambient

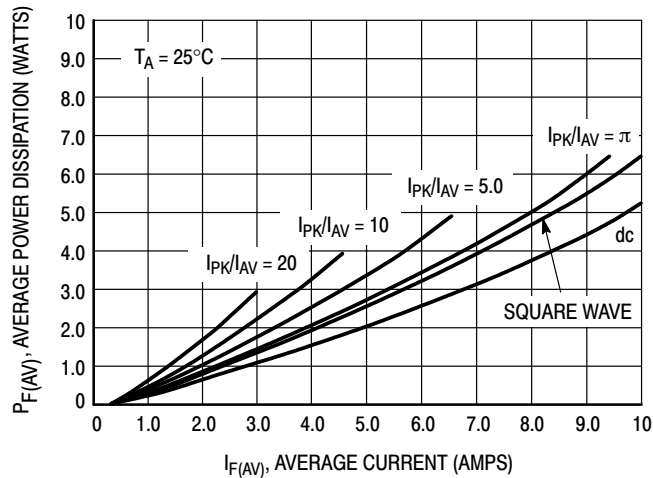


Figure 5. Forward Power Dissipation

MECHANICAL CASE OUTLINE

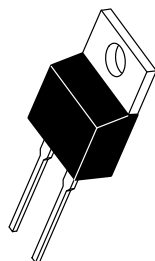
PACKAGE DIMENSIONS

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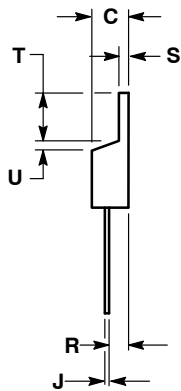
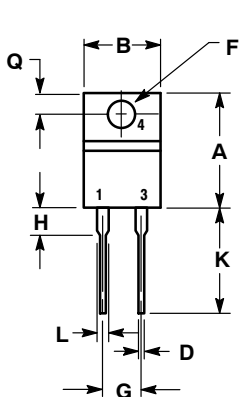


TO-220, 2-LEAD CASE 221B-04 ISSUE F

DATE 12 APR 2013



SCALE 1:1



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.595	0.620	15.11	15.75
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
H	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

STYLE 1:
PIN 1. CATHODE
2. N/A
3. ANODE
4. CATHODE

STYLE 2:
PIN 1. ANODE
2. N/A
3. CATHODE
4. ANODE

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